

PbFreeProduct

NCE15TD135LT

1350V, 15A, Trench FS II Fast IGBT

General Description:

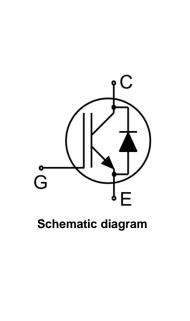
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 1350V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology offering
- Very low V_{CE(sat)}
- Positive temperature coefficient in V_{CE(sat)}
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Inductive Cooking
- Soft Switching Applications



Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE15TD135LT	TO-247	NCE15TD135LT



TO-247

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
Vces	Collector-Emitter Voltage	1350	V
V_{GES}	Gate- Emitter Voltage	±30	V
L.	Collector Current	30	А
lc	Collector Current @T _c = 100 °C	15	А
I _{Cpuls}	Pulsed Collector Current, t_p limited by T_{jmax}	45	A
-	turn off safe operating area, V_{CE} =1350V, Tj=150°C	45	A
lF	Diode Continuous Forward Current @Tc = 100 °C	15	A
IFM	Diode Maximum Forward Current	45	A
D	Power Dissipation @ T _C = 25°C	300	W
PD	Power Dissipation @T _C = 100 °C	150	W
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 to +175	°C
ΤL	Maximum Temperature for Soldering	260	°C



Thermal Characteristic

Symbol	Parameter	Value	Units
Rejc	Thermal Resistance, Junction to case for IGBT	0.50	°C/W
Rejc	Thermal Resistance, Junction to case for Diode	0.86	°C/W
R _{0JA}	Thermal Resistance, Junction to Ambient	40	°C/W

Electrical Characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Value			11
			Min.	Тур.	Max.	Units
Static Chara	cteristics				•	
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	V _{GE} =0V,I _{CE} =1mA	1350			V
ICES	Collector-Emitter Leakage Current	V _{GE} =0V,V _{CE} =1350V			5	uA
IGES(F)	Gate to Emitter Forward Leakage	V _{GE} =+30V,V _{CE} =0V			200	nA
IGES(R)	Gate to Source Reverse Leakage	V _{GE} =-30V,V _{CE} =0V			200	nA
	Collector Emitter Seturation Valtage	V _{GE} =15V,I _C =15A, Tj=25°C		1.60	1.85	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} =15V,I _C =15A, Tj=150°C		1.85		V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=1mA$, $V_{CE}=V_{GE}$	5.0		6.5	V
Dynamic Ch	aracteristics					
Cies	Input Capacitance			1430		
Coes	Output Capacitance	V _{CE} =30V,V _{GE} =0V, f=1MHz		35		pF
Cres	Reverse Transfer Capacitance			25		
Qg	Total Gate Charge			90		nC
Q _{ge}	Gate to Emitter Charge	Vcc=600V, Ic=15A V _{GE} =15V		11		nC
Q _{gc}	Gate to Collector Charge			58		nC
Switching Cl	haracteristics					
t _{d(ON)}	Turn-on Delay Time			19		
tr	Rise Time			17		20
$t_{\text{d}(\text{OFF})}$	Turn-Off Delay Time	V _{CE} =600V,Ic=15A		170		ns
t _f	Fall Time	$V_{GE}=0/15V, R_g=8\Omega$		18		
Eon	Turn-On Switching Loss	Inductive Load		0.9		
E _{off}	Turn-Off Switching Loss			0.6		mJ
Ets	Total Switching Loss			1.5		

Electrical Characteristics of the Diode ($T_c= 25^{\circ}C$ unless otherwise specified):

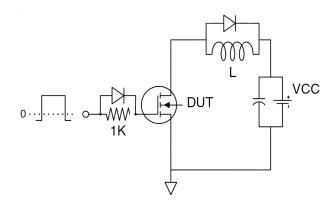
Symbol	Parameter	Test Conditions	Rating			Units
Symbol	Farameter	Test Conditions	Min.	Тур.	Max.	Units
Vfm	Diode Forward Voltage	I _F =7.5A		2.2	3.0	V
Trr	Reverse Recovery Time			120		ns
Irrm	Diode Peak Reverse Recovery Current	I⊧=7.5A, di/dt=200A/us		12		А
Qrr	Reverse Recovery Charge	di/dl=200A/us		0.72		uC
Pulse width ttp	≤380µs,δ≤2%		•	•	•	



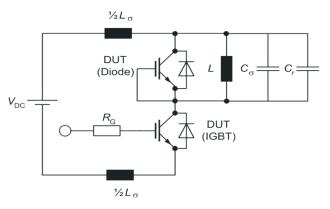


Test Circuit

1) Gate Charge Test Circuit

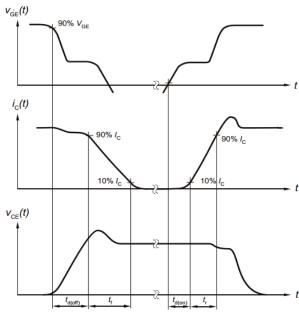


2) Switch Time Test Circuit

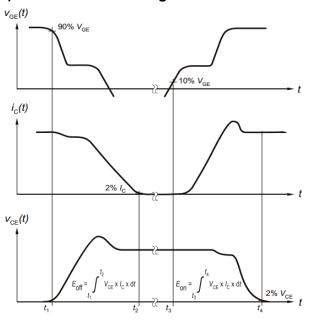


Switching characteristics

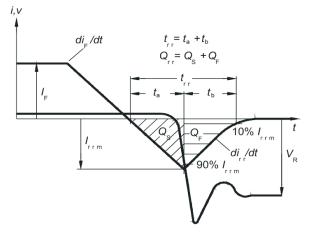
1) Definition of switching times



2) Definition of switching losses

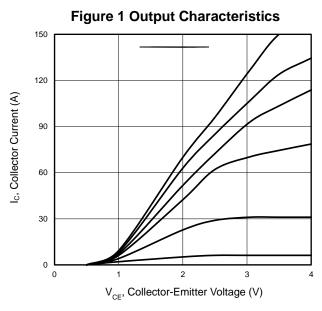


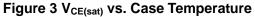
3) Definition of diode switching characteristics

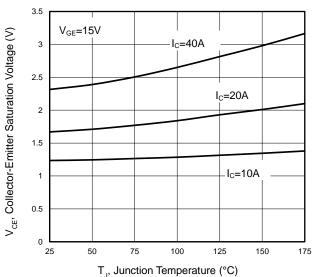




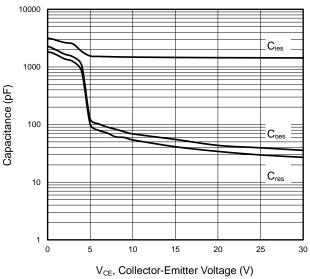
Typical Electrical and Thermal Characteristics

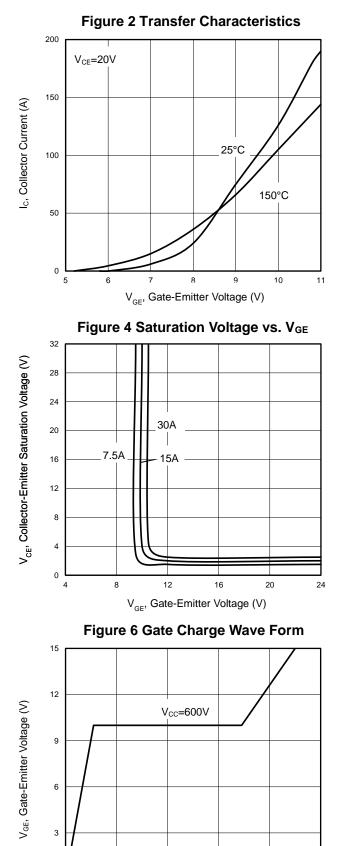












Q_G, Total Gate Charge (nC)

60

80

40

20

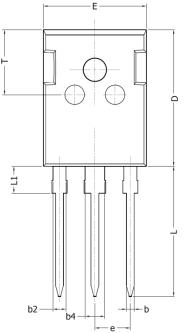
0

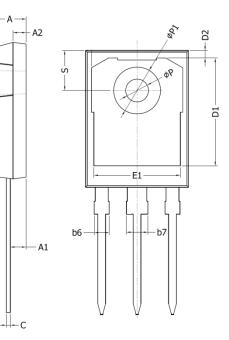
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100



TO-247-3L Package Information





O make at	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.90	5.10	0.193		
A1	2.31	2.51	0.091	0.099	
A2	1.9	2.1	0.075	0.083	
b	1.16	1.26	0.046	0.050	
b2	1.96	2.06	0.077	0.081	
b4	2.96	3.06	0.117	0.120	
b6	-	2.25	-	0.089	
b7	-	3.25	-	0.128	
С	0.59	0.66	0.023	0.026	
D	20.90	21.10	0.823	0.831	
D1	16.25	16.85	0.640	0.663	
D2	1.05	1.35	0.041	0.053	
E	15.70	15.90	0.618		
E1	13.10	13.50	0.516	0.531	
е	5.436	BSC	0.214 B	SC	
L	19.80	20.10	0.780 0.		
L1	-	4.30	- 0		
Р	3.40	3.60	0.134		
P1	7.00	7.40	0.276 0.		
S	6.05	6.25	0.238	0.246	
Т	9.80	10.20	0.386	0.402	





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